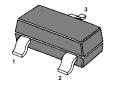
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low voltage high speed switching application

Features

- Low forward voltage
- Low reverse current





Marking Code: "ZC" SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	12	V
Reverse Voltage	V _R	10	V
Average Forward Current	Io	50	mA
Maximum Peak Forward Current	I _{FM}	150	mA
Non-Repetitive Peak Forward Surge Current (t = 10 ms)	I _{FSM}	1	А
Power Dissipation	P _d	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 50 mA	V _F	-	1	V
Reverse Current at V _R = 10 V	I _R	-	500	nA
Reverse Breakdown Voltage at $I_R = 10 \mu A$	$V_{(BR)R}$	12	-	V
Total Capacitance at $V_R = 0$, $f = 1$ MHz	C _T	-	4.5	pF



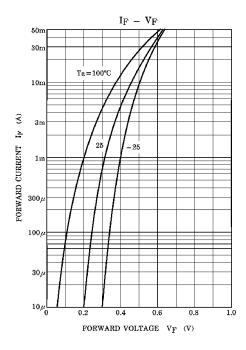


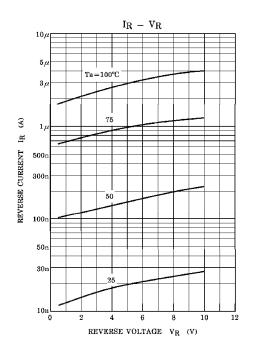


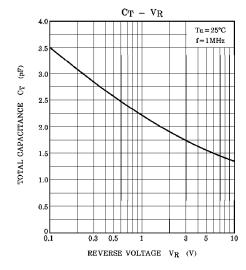


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SEMTECH ELECTRONICS LTD.











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Dated: 04/12/2007